

/ Descriptions

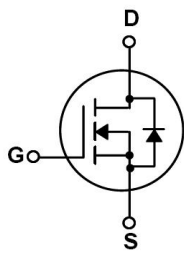
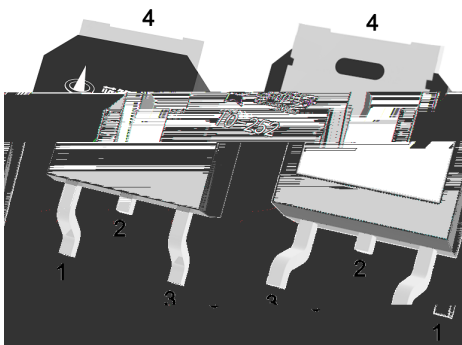
TO-252 N

N-CHANNEL MOSFET in a TO-252 Plastic Package.

/ Features $R_{DS(on)}$ C_{rss} Low $R_{DS(on)}$, low gate charge, low C_{rss} , fast switching, HF Product.**/ Applications**

DC/DC

Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit**/ Pinning**

PIN1 G

PIN 2 D

PIN 3 S

PIN 4 D

/ Marking

See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	40	V
Drain Current		$I_D(T_c=25^\circ\text{C})$	136	A
Drain Current - Pulsed		I_{DM}	280	A
Gate-Source Voltage		V_{GS}	± 20	V
Avalanche Current		I_{AS}	33	A
Single Pulsed Avalanche Energy(L=0.5mH)		E_{AS}	435	mJ
Power Dissipation		$P_D(T_c=25^\circ\text{C})$	118	W
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	
Thermal Resistance-Junction to Ambient	$t \leq 10s$	$R_{\theta JA}$	20	/W
	Steady-State		50	
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	1.06	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0V$ $I_D=250\mu A$	40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V$ $V_{GS}=0V$			1.0	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=20A$		3.0	3.5	m Ω
		$V_{GS}=4.5V$ $I_D=10A$		4.0	5.0	
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1A$			1.4	V
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$, $f=1MHz$		1.16		Ω
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		9600		pF
Output Capacitance	C_{oss}			740		
Reverse Transfer Capacitance	C_{rss}			650		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$, $V_{DS}=20V$, $I_D=20A$		51		nC
Total Gate Charge	$Q_{g(4.5V)}$			23		
Gate Source Charge	Q_{gs}			13.2		
Gate Drain Charge	Q_{gd}			3.1		

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	t					

/ Electrical Characteristic Curve

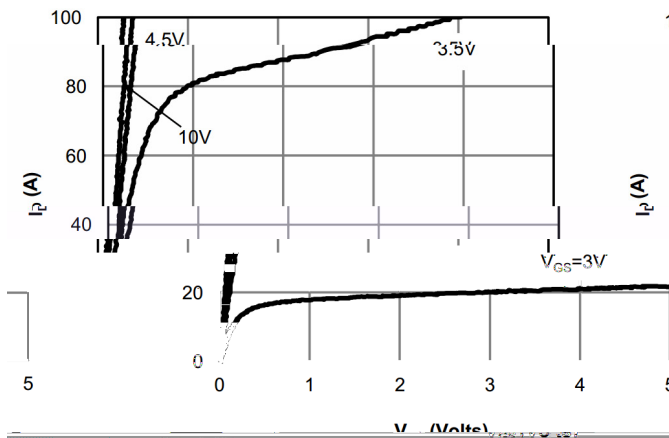


Figure 1: On-Region Characteristics

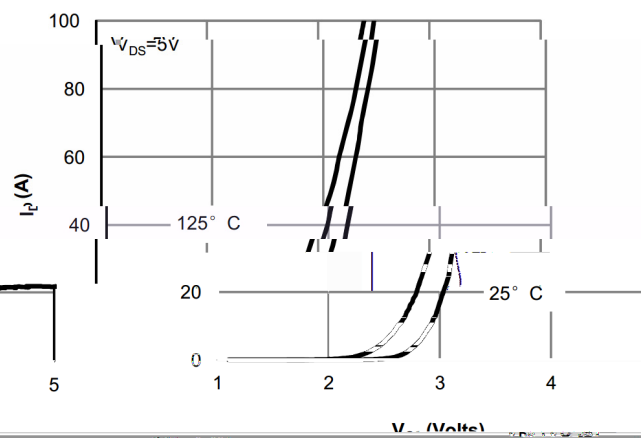


Figure 2: Transfer Characteristics

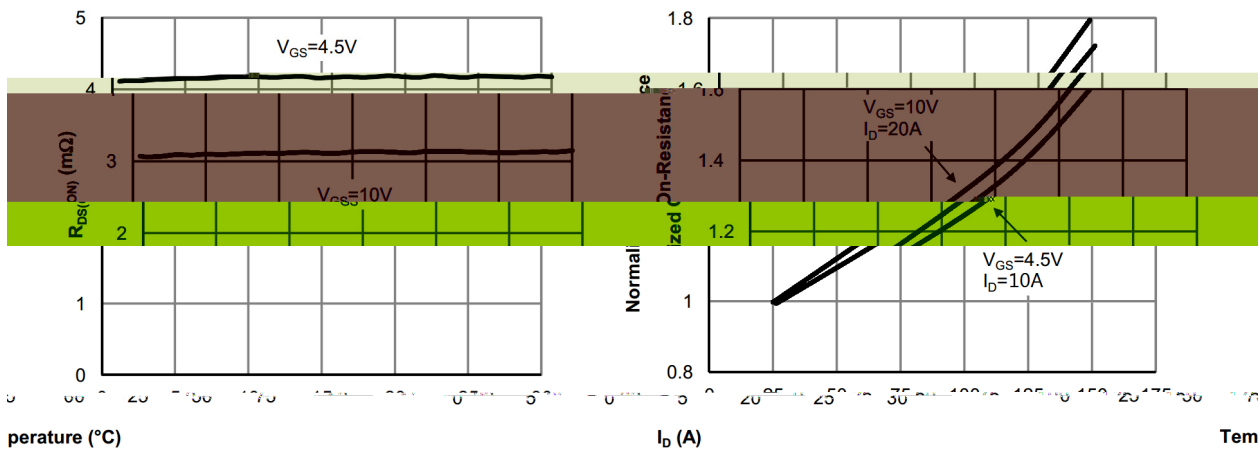


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

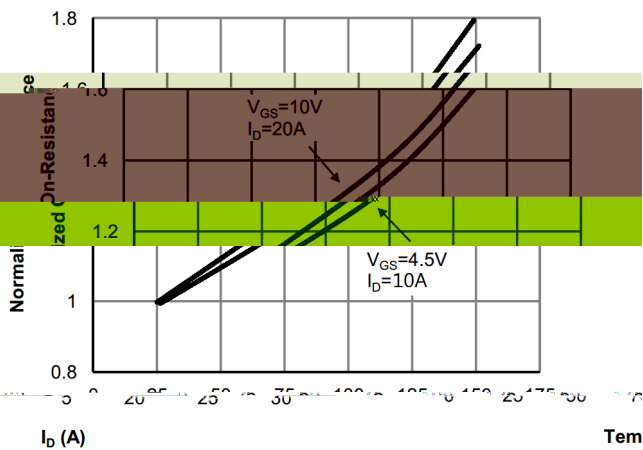
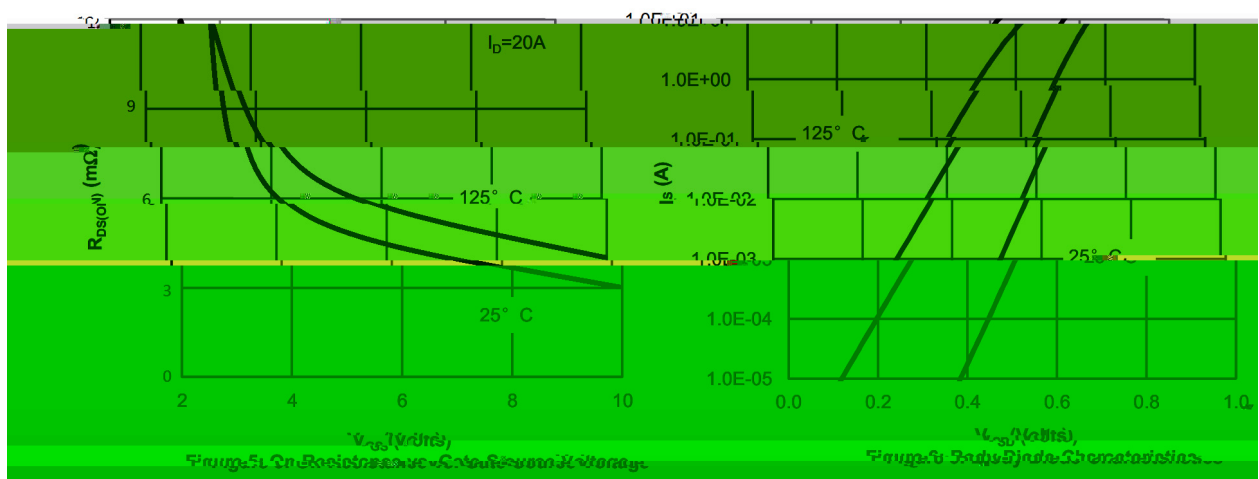
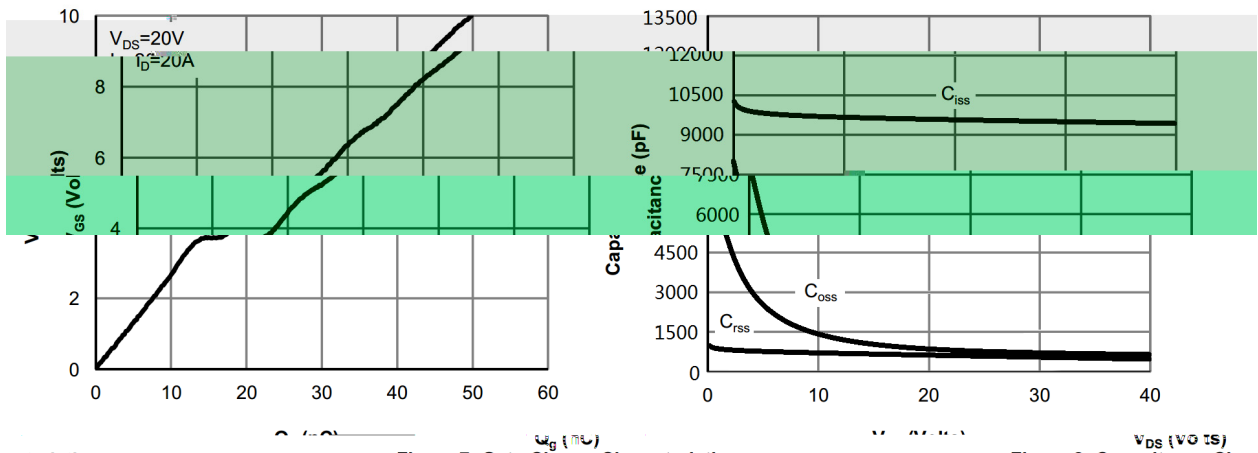


Figure 4: On-Resistance vs. Drain Current and Gate Voltage



/ Electrical Characteristic Curve



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Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Char.

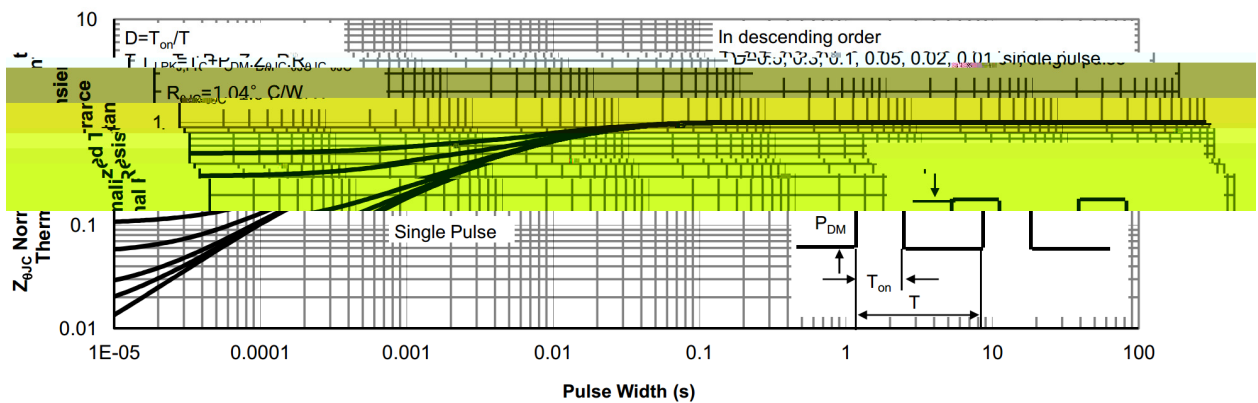
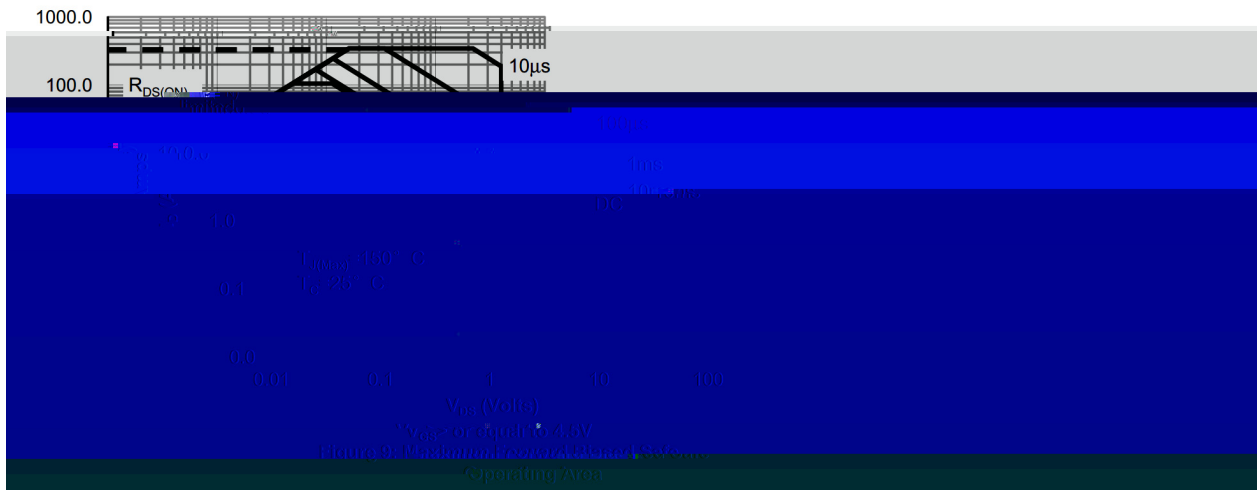
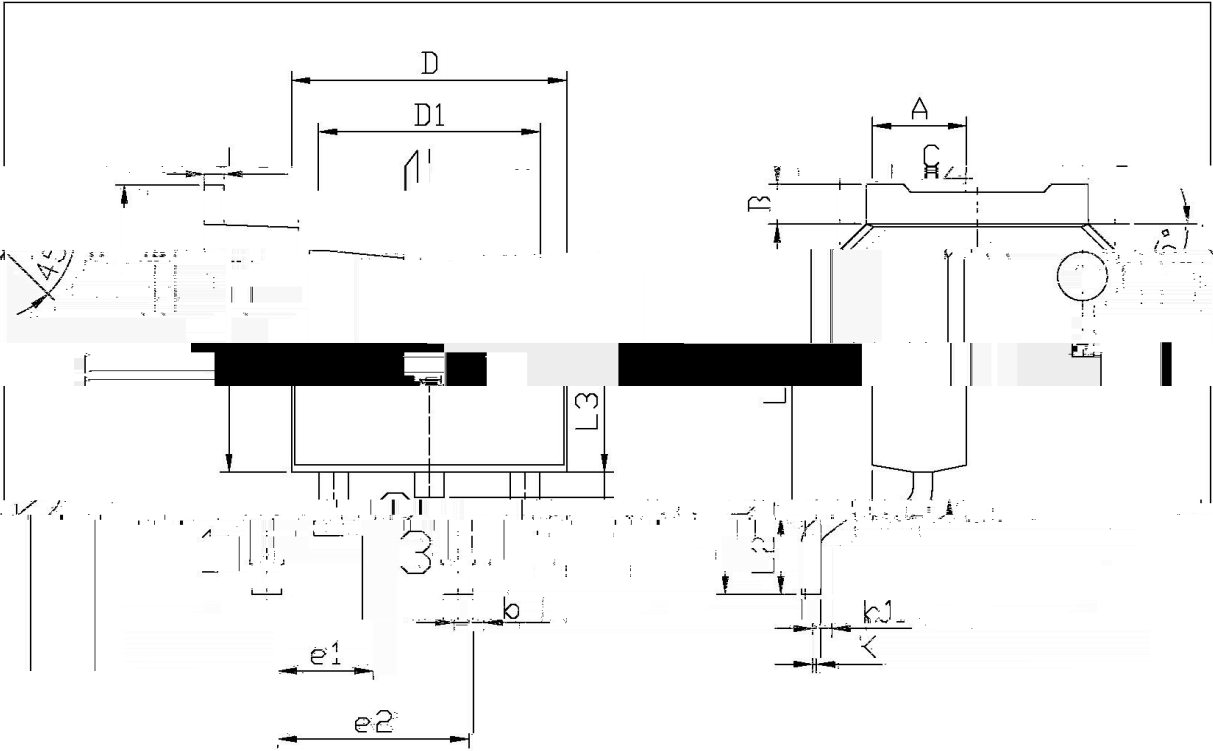


Figure 10: Normalized Maximum Transient Thermal Impedance

/ Package Dimensions

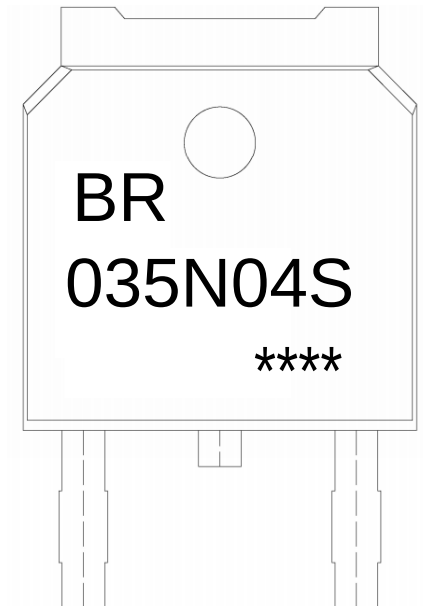


单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
F	5.95	6.25	A	0.20	0.40
B	0.95	1.25	e1	2.24	2.34
C	0.70	0.90	e2	0.20	0.40
D	10.35	10.65	b1	0.45	0.55
L3	0.60	0.90	L1	9.85	10.15
K	0.00	0.10	D1	5.10	5.40

T0-252

/ Marking Instructions



BR

035N04S

Note:

BR: Company Code

035N04S: Product Type Code

****: Lot No. Code, code change with Lot No

() / Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- | | | | |
|---|---------|-----------|---|
| 1 | 150 180 | 60 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | 2 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec
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/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box